Ã a ? d / Absolute Maximum Ratings(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Drain–Source Voltage	V_{DS}	-40	V
Gate–Body Leakage Voltage	V_{GS}	±20	V
Drain Current – Continuous	I_D	-10	A
Pulsed Drain Current	I_{DM}	-41	A
Power Dissipation	P_D	2.5	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 150	
Maximum Junction-to-Ambient	$R_{©JA}$	50	/W

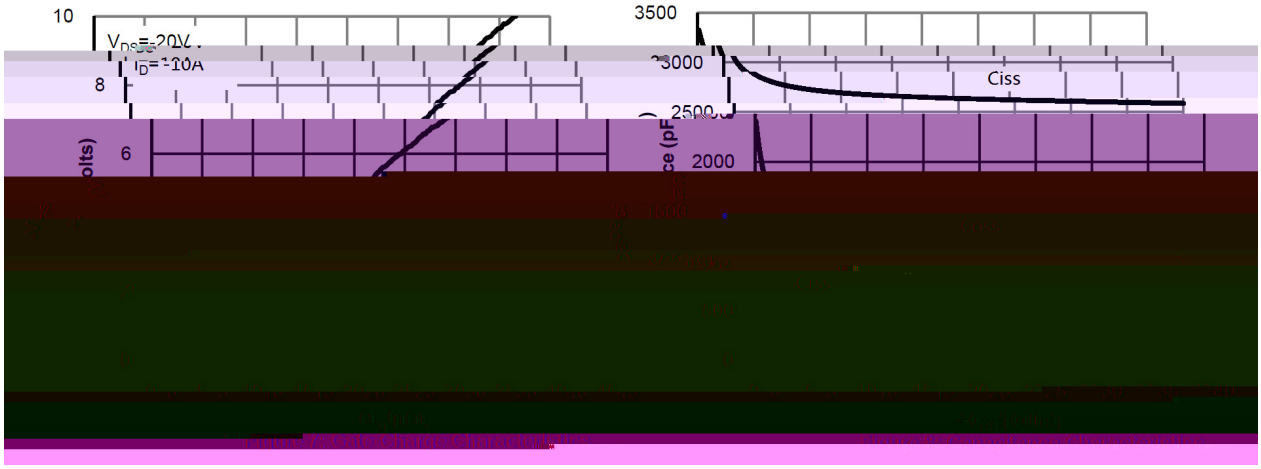
Ô4ì × ? d / Electrical Characteristics(Ta=25 ;)

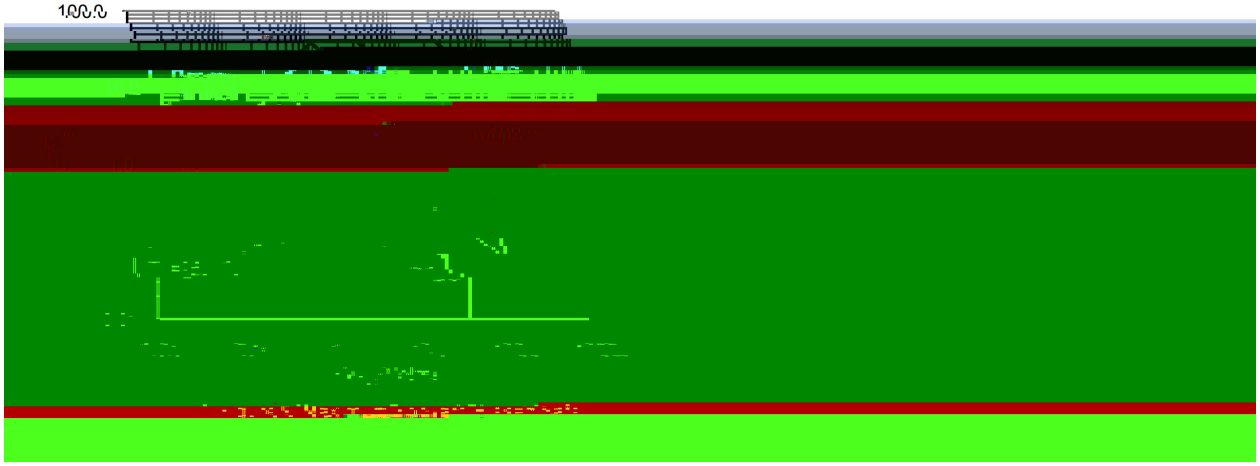
@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250 A	-40	-46.5		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V V_{GS}=0V			1.0	A
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250 A	-1.0	-1.7	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-10A		13	15	m
		V_{GS}=-4.5V I_D=-7A		17	30	
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=-1A			-1.2	V
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V, f=1MHz		6.5		
Input Capacitance	C_{iss}	V_{DS}=-25V V_{GS}=0V f=1.0MHz		2680		pF
Output Capacitance	C_{oss}			1150		
Reverse Transfer Capacitance	C_{rss}			870		
Total Gate Charge	Q_g(10V)	V_{GS}=-10V V_{DS}=-20V I_D=-10A		42		nC
Total Gate Charge	Q_g(4.5V)			18.6		
Gate Source Charge	Q_{gs}			7		
Gate Drain Charge	Q_{gd}			8.6		

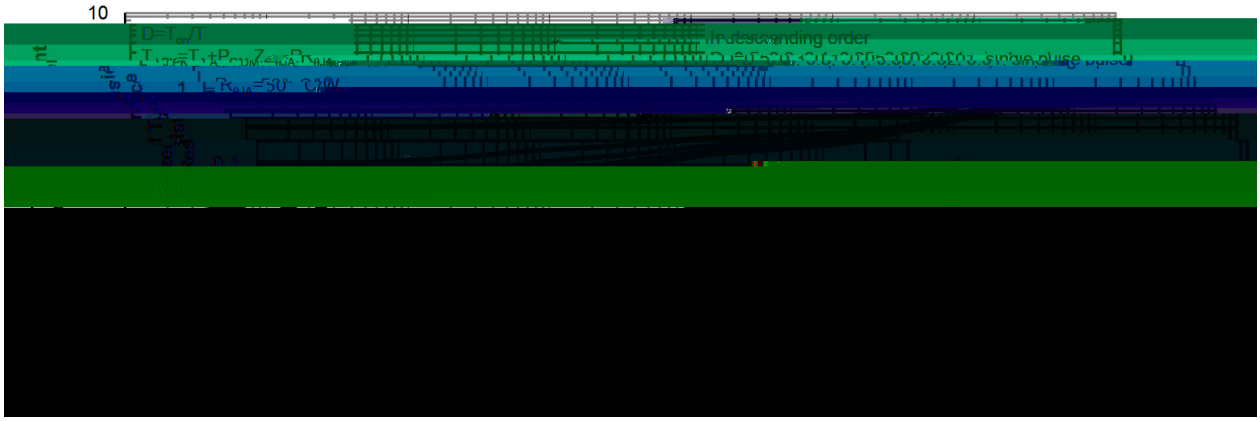
Ô4ì × ? / Electrical Characteristics(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-20V R_L=1 ¡ R_{GEN}=3		9.4		ns
Turn-On Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(off)T}$					
Turn-Off Fall Time	t_fT					

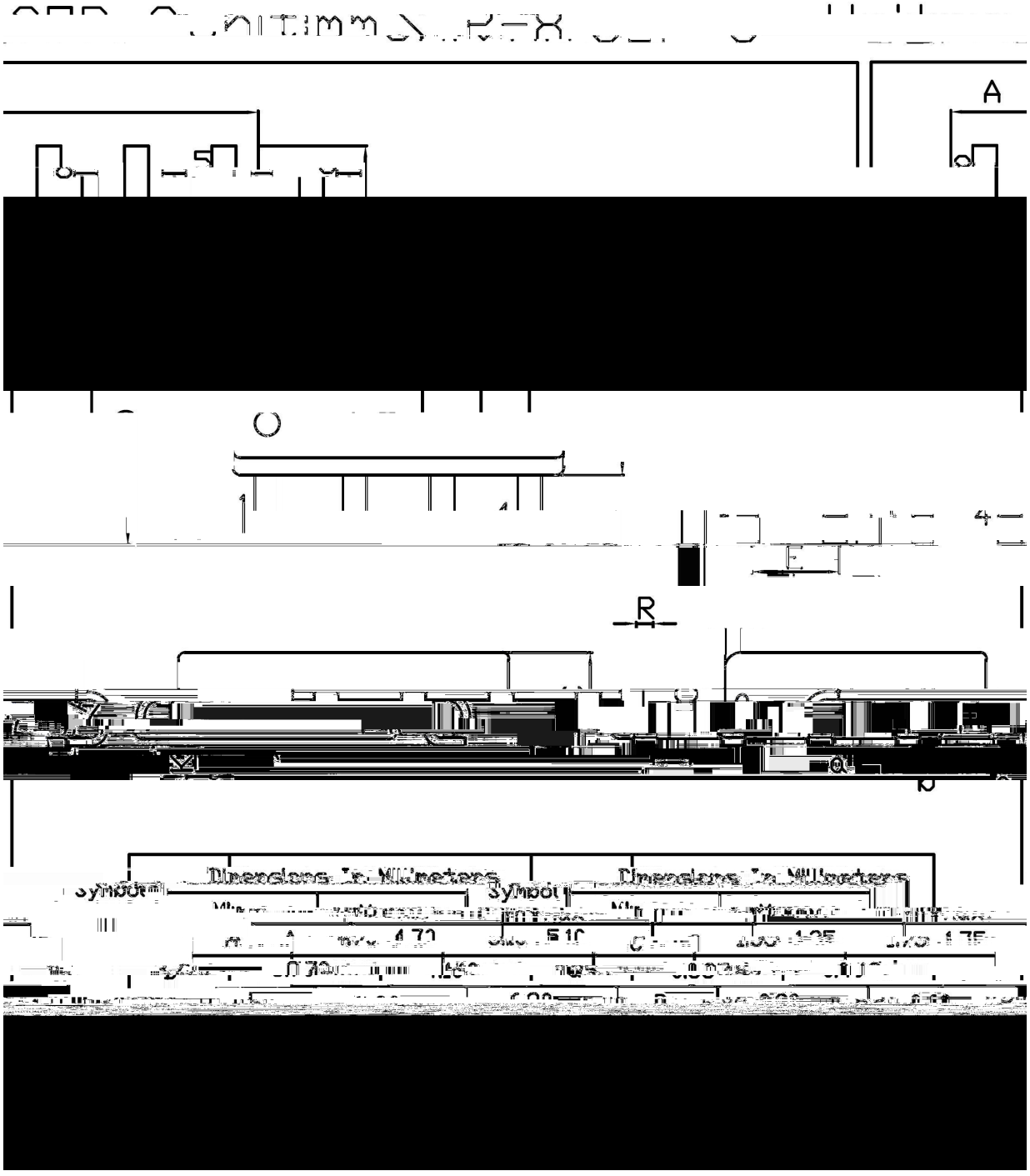
Ô ? d • Ž ¢ / Electrical Characteristic Curve



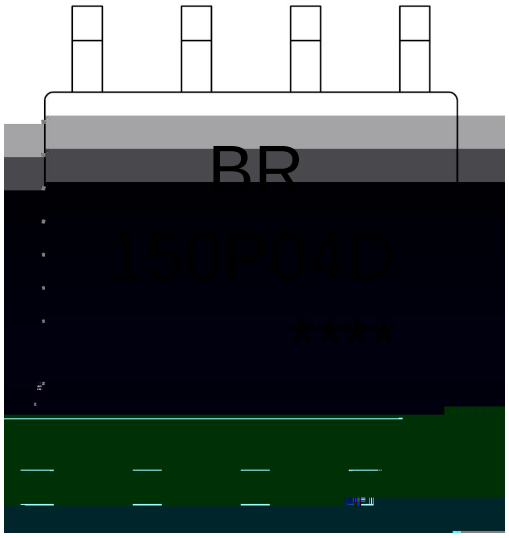




Ø ¤ =) ¢ / Package Dimensions



, M y ƒ / Marking Instructions



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Note:

BR:	Company Code
150P04D:	Product Type Code
****:	Lot No. Code, code change with Lot No